

KSD526

Power Amplifier Applications WWW.DZSC.COM

Complement to KSB596



2.Collector 3.Emitter

NPN Epitaxial Silicon Transistor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

V_{CBO} Collector-Base Voltage 80 V_{CEO} Collector-Emitter Voltage 80 V_{EBO} Emitter-Base Voltage 5 I_C Collector Current 4 I_B Base Current 0.4 P_C Collector Dissipation (T_C =25°C) 30 T_A Junction Temperature 150	Units	Value	Parameter	Symbol
VCEO Collector-Emitter Voltage 80 VEBO Emitter-Base Voltage 5 IC Collector Current 4 IB Base Current 0.4 PC Collector Dissipation (T _C =25°C) 30	V	80	Collector-Base Voltage	V _{CBO}
I _C Collector Current 4 I _B Base Current 0.4 P _C Collector Dissipation (T _C =25°C) 30	V	80	Collector-Emitter Voltage	
$\begin{array}{c c} \textbf{I}_{\text{B}} & \text{Base Current} & 0.4 \\ \textbf{P}_{\text{C}} & \text{Collector Dissipation (} \textbf{T}_{\text{C}} \text{=} 25^{\circ} \text{C)} & 30 \\ \end{array}$	V	5	Emitter-Base Voltage	V _{EBO}
P _C Collector Dissipation (T _C =25°C) 30	А	4	Collector Current	Ic
	Α	0.4	Base Current	IB
T. Junction Temperature 150	W	30	Collector Dissipation (T _C =25°C)	P _C
.j	°C	150	Junction Temperature	T _J
T _{STG} Storage Temperature - 55 ~ 1	0 °C	- 55 ~ 150	Storage Temperature	T _{STG}

Electrical Characteristics T_C=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
I _{CBO}	Collector Cut-off Current	$V_{CB} = 80V, I_{E} = 0$			30	μΑ
I _{EBO}	Emitter Cut-off Current	$V_{EB} = 5V, I_{C} = 0$			100	μΑ
BV _{CEO}	Collector-Emitter Breakdown Voltage	$I_{C} = 50 \text{mA}, I_{B} = 0$	80			V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 10 \text{mA}, I_C = 0$	5			V
h _{FE1}	DC Current Gain	$V_{CE} = 50V, I_{C} = 0.5A$	40		240	-1.16
h _{FE2}		$V_{CE} = 5V, I_{C} = 3A$	15	50		m_{V}
V _{CE} (sat)	Collector-Emitter Saturation Voltage	$I_C = 3A, I_B = 0.3A$		0.45	1.5	V
V _{BE} (on)	Base-Emitter ON Voltage	$V_{CE} = 5V, I_{C} = 3A$		1	1.5	V
f _T	Current Gain Bandwidth Product	$V_{CE} = 5V, I_{C} = 0.5A$	3	8		MHz
C _{ob}	Collector Output Capacitance	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$		90		pF

h_{FE} Classification

Classification	R	0	Υ
h _{FE}	40 ~ 80	70 ~ 140	120 ~ 240

Typical Characteristics

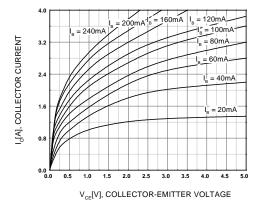


Figure 1. Static Characteristic

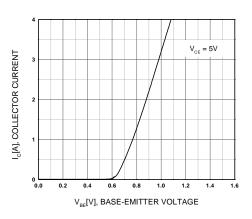


Figure 3. Base-Emitter On Voltage

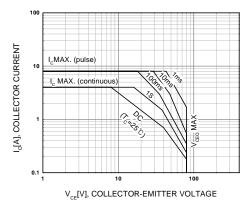


Figure 5. Safe Operating Area

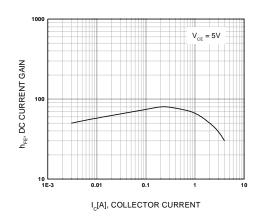


Figure 2. DC current Gain

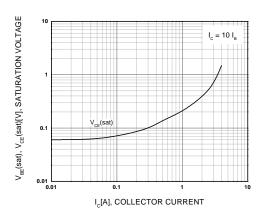


Figure 4. Collector-Emitter Saturation Voltage

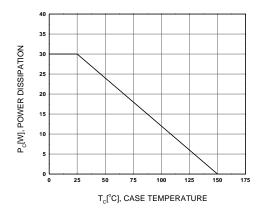
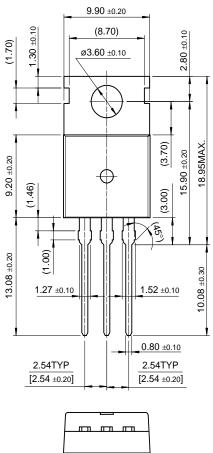


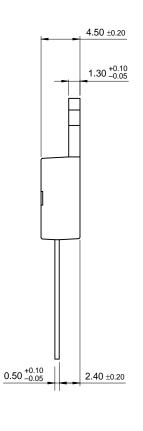
Figure 6. Power Derating

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Package Demensions

TO-220





10.00 ±0.20

Dimensions in Millimeters

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